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Substitute for form 1448A/B/PTO		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)		Application Number	To Be Assigned 10/581797
		Filing Date	June 2, 2006
		First Named Inventor	Yang YANG et al.
		Art Unit	To Be Assigned 2818
		Examiner Name	To Be Assigned Long Tran
Sheet 1 of 1	Attorney Docket Number	58086-231274	

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
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	AE				
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	AI				
	AJ				

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Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>3</sup>
		Country Code <sup>4</sup> -Number-Kind Code <sup>5</sup> (if known)				
	BA					
	BB					
	BC					
	BD					
	BE					
	BF					
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NON PATENT LITERATURE DOCUMENTS			
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	CA		
	CB		
	CC		
	CD		
	CE		

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Examiner Signature	/Long Tran/	Date Considered	12/16/2007
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Substitute for form 449/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Sheet	1	of	1	Attorney Docket Number	58086-231274
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Complete If Known	
Application Number	10/581,797-Conf.# 4944
Filing Date	June 2, 2006
First Named Inventor	Yang Yang
Art Unit	2818
Examiner Name	Not Yet Assigned Long Tran

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/LT/	AA	U.S. 6,950,331	02/12/2004	Yang YANG et al.	

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Substitute for form 1449/PTO

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STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

**Complete if Known**

Application Number	10/581,797 - Conf. # 4944
Filing Date	June 2, 2006
First Named Inventor	Yang Yang
Art Unit	2818
Examiner Name	Long K. Tran
Attorney Docket Number	58086-231274

Sheet 1 of 6

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				
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			Art Unit	2818	
			Examiner Name	Long K. Tran	
Sheet	3	of	6	Attorney Docket Number	58086-231274

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Sheet	4	of	6	Attorney Docket Number	58086-231274

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Substitute for form 1449/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)		<b>Complete If Known</b>			
		Application Number	10/581,797 – Conf. # 4944		
		Filing Date	June 2, 2006		
		First Named Inventor	Yang Yang		
		Art Unit	2818		
		Examiner Name	Long K. Tran		
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				Art Unit	2818
				Examiner Name	Long K. Tran
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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